AMENDMENT TO THE CLAIMS:

The following claim set replaces all prior versions, and listings, of claims in the application:

1. (currently amended) A photo-embossing process [[Process]] for the preparation of a polymeric relief structure [[by]] which comprises:
   a) coating a substrate with a coating comprising one or more radiation-sensitive ingredients,
   b) locally treating the coated substrate with electromagnetic radiation having a periodic or random radiation-intensity pattern, forming a latent image,
   c) polymerizing and/or crosslinking the resulting coated substrate, wherein ~~in step c)~~ a compound (Cs) is present in step c) that reduces the interfacial tension of the coated substrate.

2. (original) Process according to claim 1, wherein Cs is applied to the resulting coated substrate of step b).

3. (original) Process according to claim 1, wherein Cs is already present in the coating used in step a).

4. (previously presented) Process according to claim 1, wherein the radiation-sensitive ingredient(s) in step a) comprise(s) one or more monomers, in combination with one or more polymerization initiators.

5. (previously presented) Process according to claim 1, wherein in step a) the coating also comprises a polymer.

6. (original) Process according to claim 4, wherein the polymerization initiator is a mixture of a photo-initiator and a thermal initiator.

7. (previously presented) Process according to claim 1, wherein the coating is a solid film after evaporation of the volatile solvent.

8. (previously presented) Process according to claim 1, wherein a lithographic mask is used in direct contact with the photo-polymer film.

9. (previously presented) Process according to claim 1, wherein the electromagnetic radiation is UV-light in combination with a mask.

10. (previously presented) Process according to claim 1, wherein the treatment in step b) is by the use of light interference/holography.

11. (previously presented) Process according to claim 1, wherein the substrate comprises a polymer.

12. (original) Process according to claim 5, wherein the polymer in the coating of step a) has a weight averaged molecular weight (Mw) of at least 20,000 g/mol.

13. (previously presented) Process according to claim 5, wherein the polymer in the coating of step a) has a glass transition temperature of at least 300 K.

14. (previously presented) Process according to claim 5, wherein the polymer is dissolved in the monomer (s) of the radiation-sensitive coating used in step a).

15. (previously presented) Process according to claim 1, wherein the ingredient (s) in the radiation-sensitive coating is/are selected from the group comprising (meth-)acrylates, epoxies, vinyl ethers, styrenes, and thiol-enes.

16. (previously presented) Process according to claim 1, wherein Cs reduces the interfacial tension with at least 10 mJ/m^2.

17. (previously presented) Process according to claim 1, wherein Cs is applied in an amount of from 0.05-5 wt%, relative to the amount of the coating.

18. (currently amended) Polymeric relief structure obtained by the ~~obtainable through a~~ process according to claim 1.

19. (original) Polymeric relief structure according to claim 18, wherein the aspect-ratio (AR) is at least 0.12, the AR being the ratio between the relief height and the distance between neighboring reliefs

20. (currently amended) Polymeric relief structure according to claim 18, wherein the maximum absolute value of the curvature (I $k_{,max}$ I) is at least 0.35~~, more preferably at least 0.45, and even more preferably at least 0.65~~ μm^{-1}.

21. (previously presented) Polymeric relief structure according to claim 18, wherein the AR is at least 0.2.

22. (previously presented) Polymeric relief structure according to claim 18, wherein I k_{max} I is at least 0.7 μm^{-1}.

23. (previously presented) Process according to claim 1, wherein step b) is performed at a temperature between 175 and 375 K.

24. (previously presented) Process according to claim 1, wherein step c) is performed at a temperature of between 300 and 575 K.

25. (previously presented) A method of managing light comprising incorporating a polymeric relief structure according to claim 18 in a light- management element.

26. (previously presented) Method according to claim 25 wherein the polymeric relief structure is incorporated in diffractive- or orholographic-optical elements.

27. (previously presented) A method for replication of organic or inorganic matter comprising using as a replication master a polymeric relief structure according to claim 18.

28. (new) Polymeric relief structure according to claim 18, wherein the maximum absolute value of the curvature (I $k_{,max}$ I) is at least 0.45 μm^{-1}.

29. (new) Polymeric relief structure according to claim 18, wherein the maximum absolute value of the curvature (I $k_{,max}$ I) is at least 0.65 μm^{-1}.